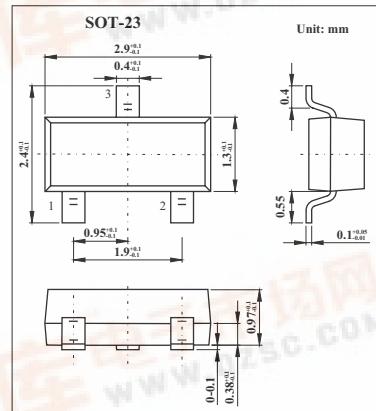


SMD Type

Diodes

Silicon Schottky Barrier Diode

HSM107S



■ Features

- Low VF and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	VR	8	V
Peak forward current	IFM	0.1	A
Non-Repetitive Peak forward surge current	IFSM (Note 1)	0.5	A
Average rectified current	Io	50	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note

1. Square wave, 10ms

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	VR	VR = 1.0 mA	8			pF
Reverse current	IR	VR = 5 V			30	μA
Forward voltage	VF	IF = 10 mA			0.3	V
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	100			V

Note

1. Failure criterion ; IR ≥ 60 μ A at VR = 5 V

■ Marking

Marking	C5
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